Icemos Technology Ltd Product Specification 1003.007604 Issue Date 05 July 2010 08:39:48

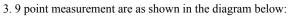
| Part Number | Customer | |
|-------------|----------|--|

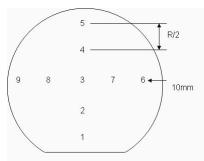
| Category | | Parameter | Specification | Measurement Method |
|---------------|------|---------------------------------|---|--------------------------------------|
| OverallWafer | 1.0 | Diameter | 100.00 +/- 0.50 mm | |
| | 2.0 | Primary Flat Orientation | {110}+/-1 degree | Wafer Vendor |
| | 3.0 | Primary Flat Length | 32.50 +/- 2.50 mm | Wafer Vendor |
| | 4.0 | Secondary Flat Orientation | none / semi std | wafer vendor |
| | 5.0 | Overall Thickness | 525.00 +/- 25.00 μm | ADE, 100% |
| | 6.0 | Total Thickness Variation (TTV) | <10.00um | ADE, 100% measurement |
| | 7.0 | Bow | <40.00μm | ADE to ASTM F534, 20% |
| | 8.0 | Warp | <40.00μm | ADE to ASTM F657, 20% |
| | 9.0 | Edge Chips | 0 | Bright Light, 100% (note 2) |
| | 10.0 | Edge Exclusion | 5mm | |
| HandleSilicon | 11.0 | Handle Growth Method | CZ | Wafer Vendor |
| | 12.0 | Handle Orientation | {100} +/- 1 degree | Wafer Vendor |
| | 13.0 | Handle Thickness | 525.00 +/- 25.00 μm | ADE, 100% |
| | 14.0 | Handle Doping Type | N | Wafer Vendor |
| | 15.0 | Handle Dopant | Phosphorous | Wafer Vendor |
| | 16.0 | Handle Resistivity | 1 - 100 Ohmem | Wafer Vendor |
| | 17.0 | Backside Finish | Polished with 1.8um +/- 0.2um oxide and lasermark, no polysilicon. Planarise after phosphorous deposition of poly | Wafer Vendor |
| DeviceSilicon | 18.0 | LPD Count | <30.00pces | @0.3um, Tencor 6220 particle counter |
| | 19.0 | Scratches | 0 | Bright Light, 100% (note 2) |
| | 20.0 | Haze | none | Bright Light, 100% (note 2) |
| | 21.0 | Surface | front side prime polished (before oxide and poly deposition) | Guaranteed by process |
| | 23.0 | Device Field Oxidation | 20,000.00 +/- 1,000.00 A | Nanospec 4%, 5pt |
| Trench | 24.0 | Poly refill thickness | 20000A +/- 1000A, doped as per the schedule in notes. Sheet resistance of poly <2.8 Ohms per sq | 4 pt probe 100% |

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| Part Number | | Customer | | |
|-------------------|--|---|--------------------|--|
| Category | Parameter | Specification | Measurement Method | |
| Shipping Details | Wafer per box : | Max 25 | | |
| | Packaging: | Taped Polypropylene Wafer Box Empak, Ultrapak, 100.00mm Antistatic Double Bagging | | |
| | Lot Shipment Data | Device Thickness Bow / Warp Data Handle and SOI Thickness | | |
| Explanatory Notes | 1. Microscope inspec | tion performed using microscope scan as below. 5x objective. | | |
| | 2. All bright light inspections performed exclude all wafer area outside the edge exclusion defined in Overall | | | |

Wafer, Edge Exclusion. High intensity bright lamp inspection as per ASTM F523.





Additional Information